



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:
Hwang, et al

Serial No.: 10/092,456

Confirmation No.: 1212

Filed: March 6, 2002

For: Etching Methods for a Magnetic Memory Cell Stack

Commissioner for Patents
Washington, D.C. 20231

Dear Sir:

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Group Art Unit: 2818

Examiner: D. A. Le

CERTIFICATE OF MAILING
37 CFR 1.8

I hereby certify that this correspondence is being deposited on February 24, 2003 with the United States Postal Service as First Class Mail in an envelope addressed to: Commissioner for Patents, Washington, D C 20231

Date

Signature

RESPONSE TO RESTRICTION REQUIREMENT DATED JANUARY 24, 2003

In response to the Restriction Requirement dated January 24, 2003, having a shortened statutory period for response set to expire on February 24, 2003, please enter this response and reconsider the claims pending in the application for reasons discussed below. Although Applicants believe that no fee is due in connection with this response, the Commissioner is hereby authorized to charge counsel's Deposit Account No. 20-0782/APPM/6437/BTP, for any fees, including extension of time fees or excess claim fees, required to make this response timely and acceptable to the Office.

IN THE CLAIMS:

Please amend the claims as follows:

11. A method for plasma etching in a plasma reactor, comprising:
positioning a work piece in the plasma reactor, the work piece including at least
one magnetic material layer selected from NiFe, CoFe, NiFeCo, and Ru;

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